

A fully integrated 10-bit 100 MS/s SAR ADC with metastability elimination for the high energy physics experiments

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The demand of high speed, low power analog-to-digital converter (ADC) is growing fast in future high energy physics experiments or in upgrade of current detectors. Also, the ADC becomes more and more critical in the front-end application specific integrated circuit (ASIC) design. Based on these considerations, a fully integrated, 10-bit 100MS/s successive approximation register (SAR) ADC with metastability elimination technique for the high energy physics experiments has been developed.

The ADC is composed of an internal bandgap biasing circuitry, a high bandwidth reference buffer, a digital clock management unit, and 10-bit digital output buffers with unsigned binary format. A non-binary weight capacitor digital-to-analog converter (C-DAC) network and a hybrid capacitor switching architecture are used to increase conversion accuracy and speed. A metastability elimination technique is employed to avoid comparator metastability, and then reduce the conversion error rate (CER) at a high-speed asynchronous operation. The full custom logic cells without floating nets are designed to improve the performance of the radiation hardness.

The ADC was designed and fabricated in a 40 nm CMOS process. It occupies 0.078 mm² active area including references and the core area is only 0.037 mm². The measured power consumption of the ADC core is 1.32 mW and the total power consumption is 8.5 mW including references under a 1.1V supply. The resulting figure-of-merit (FOM), for sampling rate 100 MS/s, is 135 fJ/conversion-step. The largest power goes to a robust reference buffer that comprise a fully integrated ADC ASIC. It achieves a good dynamic performance with ENOB ~ 9.3bit at 100MS/s with 14.97MHz input signal. The measured spurious free dynamic range (SFDR), total harmonic distortion (THD) and signal-to-noise ratio (SNR) are 72dB, -69dB, 58dB, respectively. And the measured DNL and INL are +0.67/-0.54 LSB and +0.62/-0.4 LSB respectively.

Submission declaration

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